imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C
	52mΩ @ V _{GS} = 10V	4A
30V	65mΩ @ V _{GS} = 4.5V	ЗA
	85mΩ @ V _{GS} = 2.5V	2A

Applications

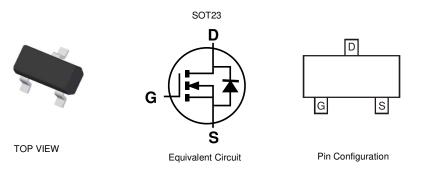
- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays

Features

- Low On-Resistance:
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMG3402L-7	SOT23	3000/Tape & Reel
DMG3402L-13	SOT23	10000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://:www.diodes.com/products/packages.html.

Marking Information

I	N 32	ΥM

N32 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006)

M = Month (ex: 9 = September)

Date Code Key

	1											
Year	201	2	2013		2014	20	15	2016		2017	2	2018
Code	Z		А		В	(2	D		E		F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±12	V
Drain Current (Note 5)	I _D	4.0	А
Body-Diode Continuous Current (Note 5)	ls	1.5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	1.4	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 5)	R _{0JA}	90	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

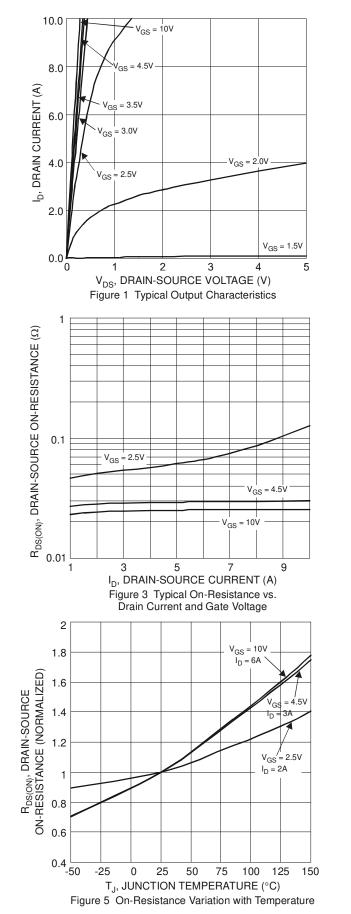
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

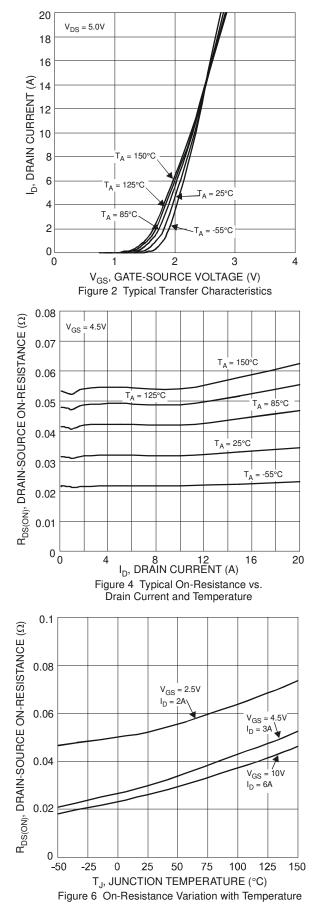
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 6)								
Drain-Source Breakdown Voltage	BV _{DSS}	30	_		V	$V_{GS} = 0V, I_D = 250 \mu A$		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 30V, V_{GS} = 0V$		
Gate-Body Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 6)								
Gate Threshold Voltage	V _{GS(th)}	0.6	—	1.4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$		
			—	52		$V_{GS} = 10V, I_D = 4A$		
Static Drain-Source On-Resistance	R _{DS(ON)}	_	—	65	mΩ	$V_{GS}=4.5V,I_{D}=3A$		
			—	85		$V_{GS} = 2.5V, I_D = 2A$		
Forward Transconductance	Y _{fs}	_	6.6		S	$V_{DS} = 5V, I_D = 3.1A$		
Source-Drain Diode Forward Voltage	V _{SD}	_	—	1.16	V	$V_{GS} = 0V, I_{S} = 2.0A$		
DYNAMIC CHARACTERISTICS(Note 7)								
Gate Resistance	Rg	_	2.2	—	Ω	$V_{DS} = 0V, V_{GS} = 0V,$ f = 1MHz		
Total Gate Charge (10V)	Qg		11.7		nC	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \ V, \ V_{DS} = 15 V, \\ I_D = 4 \ A \end{array}$		
Total Gate Charge (4.5V)	Qq	_	5.5		nC			
Gate-Source Charge	Q _{gs}	_	1.1		nC	$V_{GS} = 10 V, V_{DS} = 15V,$		
Gate-Drain Charge	Q _{gd}	_	1.8		nC	$I_D = 4 A$		
Turn-On Delay Time	t _{D(on)}		1.9		ns			
Turn-On Rise Time	tr	_	1.6		ns	$V_{DD} = 15V, V_{GEN} = 10V,$		
Turn-Off Delay Time	t _{D(off)}		10.3		ns	$R_{GEN} = 3\Omega, R_L = 3.75\Omega$		
Turn-Off Fall Time	tf		2.0		ns]		
Input Capacitance	C _{iss}		464		pF			
Output Capacitance	Coss	_	49.5		pF	$V_{DS} = 15V, V_{GS} = 0V$		
Reverse Transfer Capacitance	C _{rss}	_	43.8		pF	f = 1.0MHz		

Notes:

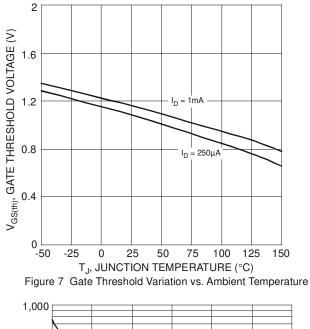
Device mounted on FR-4 PCB. t ≤5 sec.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.

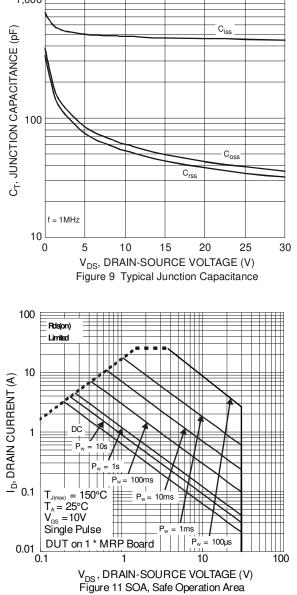


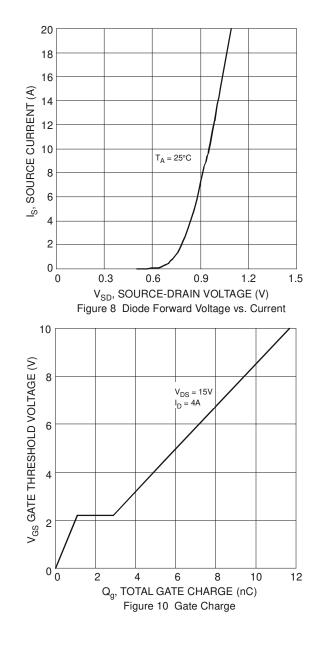




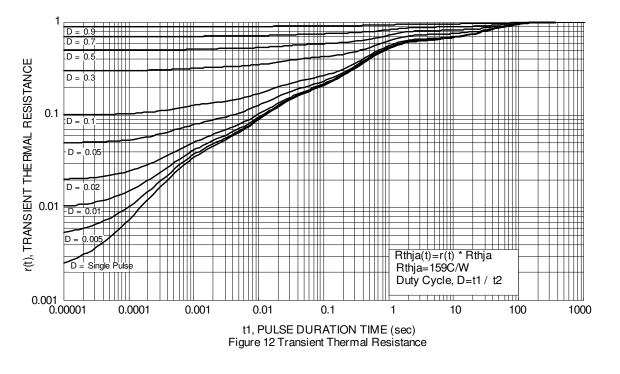






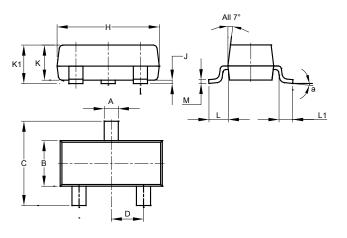






Package Outline Dimensions

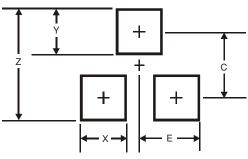
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а		8°				
All	Dimens	ions in	mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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